

High resolution vertexing based on CMOS sensors with microsecond time stamping

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- Sensor design : coll. with IRFU-Saclay -

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- *Development of a fast CMOS sensor (AROM) with μs level timestamping*
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- *Example of inner tracker application: the ILD SIT*
- *Summary*

CMOS Pixel Sensors for the ILD-VXD

- **Two types of CMOS Pixel Sensors (CPS):**

- ✳ **Inner layers** ($\lesssim 300 \text{ cm}^2$) : priority to read-out speed & spatial resolution

- ↪ small pixels ($16 \times 16 / 80 \mu\text{m}^2$) with binary charge encoding

- ↪ $t_{r.o.} \sim 50 / 10 \mu\text{s}$; $\sigma_{sp} \lesssim 3 / 6 \mu\text{m}$

- ✳ **Outer layers** ($\sim 3000 \text{ cm}^2$) : priority to power consumption and good resolution

- ↪ large pixels ($35 \times 35 \mu\text{m}^2$) with 3-4 bits charge encoding

- ↪ $t_{r.o.} \sim 100 \mu\text{s}$; $\sigma_{sp} \lesssim 4 \mu\text{m}$

- ✳ Total VXD instantaneous/average power $< 700/20 \text{ W}$ ($0.35 \mu\text{m}$ process)

- **2-sided ladder concept for inner layer :**

- ✳ Square pixels ($16 \times 16 \mu\text{m}^2$) on internal ladder face ($\sigma_{sp} < 3 \mu\text{m}$)

- & Elongated pixels ($16 \times 80 \mu\text{m}^2$) on external ladder face ($t_{r.o.} \sim 10 \mu\text{s}$)

- **Sensor final prototypes :** fabricated in Q4/2011

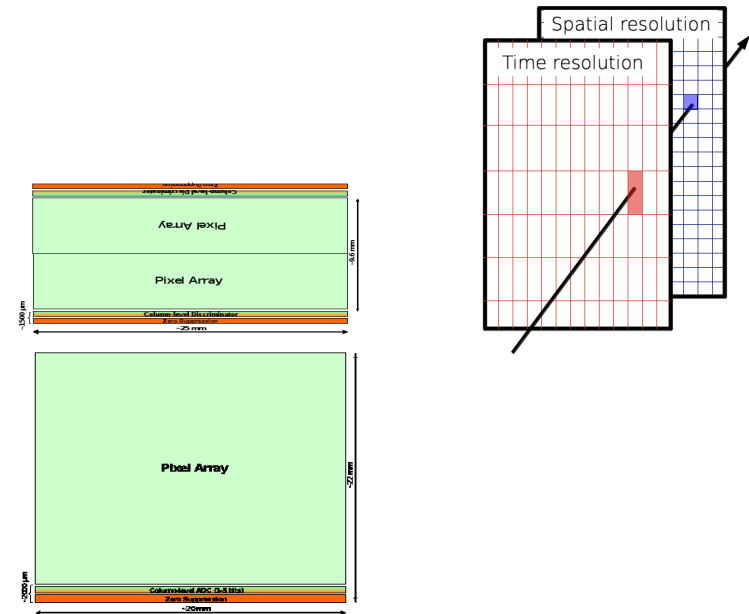
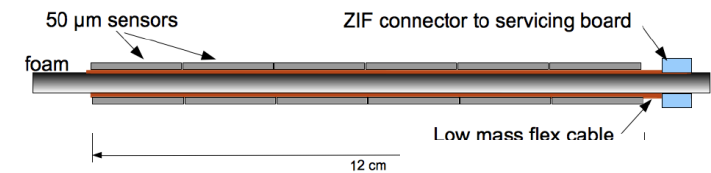
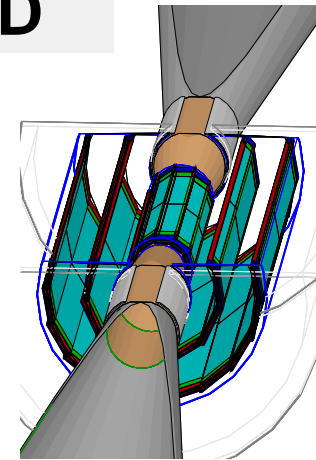
- ✳ **MIMOSA-30:** inner layer prototype with 2-sided read-out

- ↪ one side : 256 pixels ($16 \times 16 \mu\text{m}^2$)

- ↪ other side : 64 pixels ($16 \times 64 \mu\text{m}^2$)

- ✳ **MIMOSA-31:** outer layer prototype

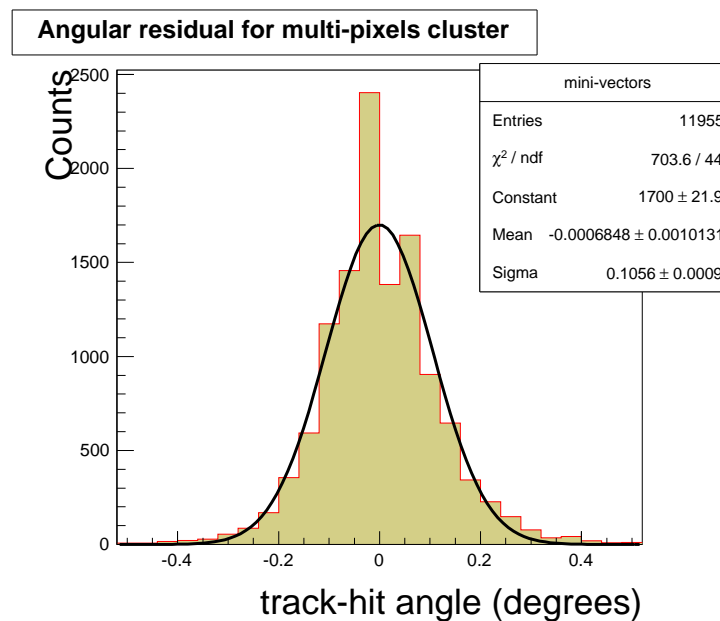
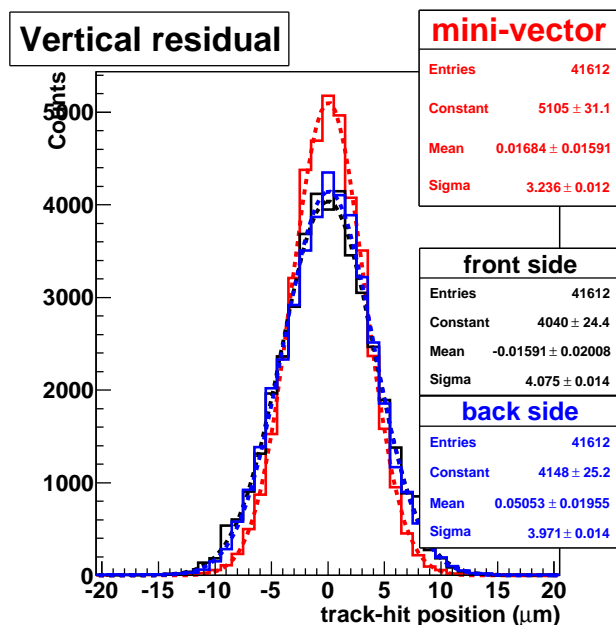
- ↪ 48 col. of 64 pixels ($35 \times 35 \mu\text{m}^2$) ended with 4-bit ADC



2-Sided Ladder Beam Test Results

- **PLUME prototype-2010 tested at SPS in Nov. 2011:**

- ✧ *Beam telescope : 2 arms, each composed of 2 MIMOSA-26 sensors*
- ✧ *DUT : 1 PLUME ladder prototype (0.6 % X_0)*
 - ↳ *6 MIMOSA-26 sensors on each ladder face (8 Mpixels)*
- ✧ *CERN-SPS beam : $\gtrsim 100$ GeV " π^- " beam*
- ✧ *BT (track extrapolation) resolution on DUT : $\sim 1.8 \mu m$*
- ✧ *Studies with PLUME perpendicular and inclined ($\sim 36^\circ$) w.r.t. beam line*
- ✧ *Preliminary results (no pick-up observed): combined impact resolution & pointing resolution*



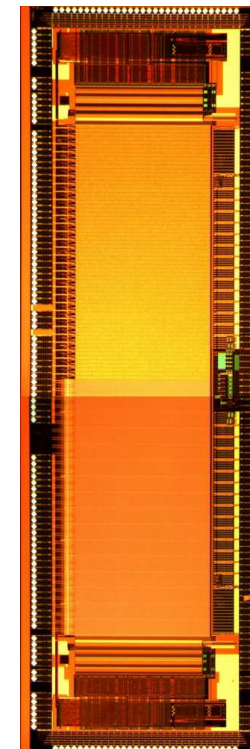
- **New PLUME prototype under construction with 0.35 % X_0 (X-section) \rightarrow beam tests in Q4/2012**

CMOS Pixel Sensors: Status of Baseline Devt

- **MIMOSA-30: prototype for ILD-VXD innermost layer**



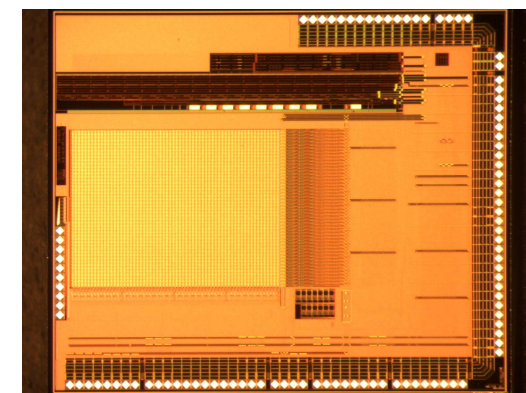
- ✧ 0.35 CMOS μm process with high-resistivity epitaxy
- ✧ in-pixel CDS, rolling shutter read-out, binary sparsified output
- ✧ **high resolution side : pixels of $16 \times 16 \mu m^2 \Rightarrow$ expect $\sigma_{sp} < 3 \mu m$**
 - 128 columns (discri) & 8 col. (analog) of 256 rows (final scale)
 - read-out time $\lesssim 50 \mu s$
- ✧ **time stamping side : pixels of $16 \times 64 \mu m^2 \Rightarrow t_{r.o.} \sim 10 \mu s$**
 - (expect $\sigma_{sp} \sim 6 \mu m$)
 - 128 columns (discri) and 8 col. (analog) of 64 rows (final scale)
 - lab tests positive : $N \sim 15 e^-$ ENC & discri. all OK for $t_{r.o.} = 10 \mu s$
- ✧ beam tests (CERN-SPS) in June/July '12 $\Rightarrow \sigma_{sp}, \epsilon_{det},$ fake rate



- **MIMOSA-31: prototype for ILD-VXD outer layers**



- ✧ pixels of $35 \times 35 \mu m^2$ (power saving)
- ✧ 48 columns of 64 pixels ended with 4-bit ADC (1/10 of full scale chip)
 - \hookrightarrow expect $\sigma_{sp} \lesssim 3.5 \mu m$
- ✧ $t_{r.o.} \sim 10 \mu s$ (1/10 of full scale chip)
- ✧ beam tests (DESY) in Q1/2013 $\Rightarrow \sigma_{sp}, \epsilon_{det},$ fake rate



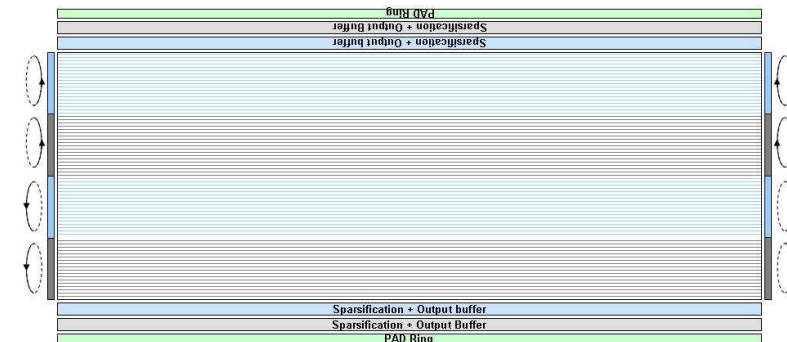
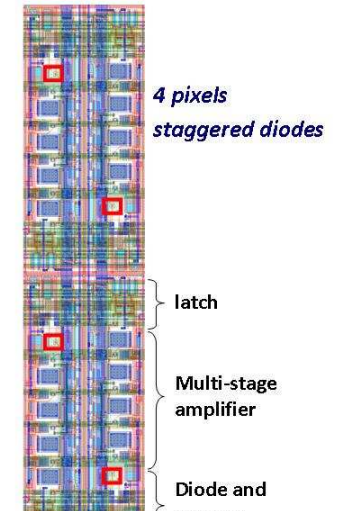
Read-Out Acceleration

● Motivations

- ✧ robustness w.r.t. predicted BG rate (keep small inner radius, no Anti-DID, ..)
- ✧ standalone inner tracking capability (e.g. soft tracks, SiD ?)
- ✧ compatibility with high-energy running: beam BG at $\sqrt{s} \gtrsim 1$ TeV
 - ↳ beam BG ($\gtrsim 1$ TeV) at least $3 \times$ BG (500 GeV)

● How to accelerate the elongated pixel read-out

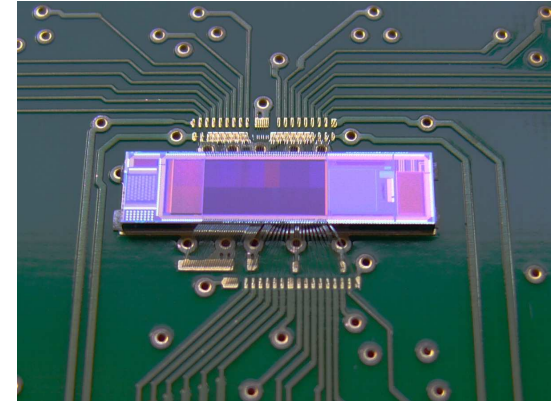
- ✧ elongated pixel dimensions allow for in-pixel discriminators $\Rightarrow \geq 2$ faster r.o. ▷ ▷
- ✧ read out simultaneously 2 or 4 rows \Rightarrow 2-4 faster r.o./side
- ✧ subdivide pixel area in 4-8 sub-arrays read out in // \Rightarrow 2-4 faster r.o.
- ▷ 0.18 μm CMOS process needed
 - ↳ 6-7 ML,, design compactness, in-pixel CMOS T, ...
- ✧ conservative step: 2 discri./column **end** (22 μm wide)
 - \Rightarrow read out 2 rows simultaneously
 - ↳ 1st stage improvement: 50/10 $\mu s \rightarrow$ 25/5 μs
 - (works even with 0.35 μm technology)



0.18 μm Technology Prototyping

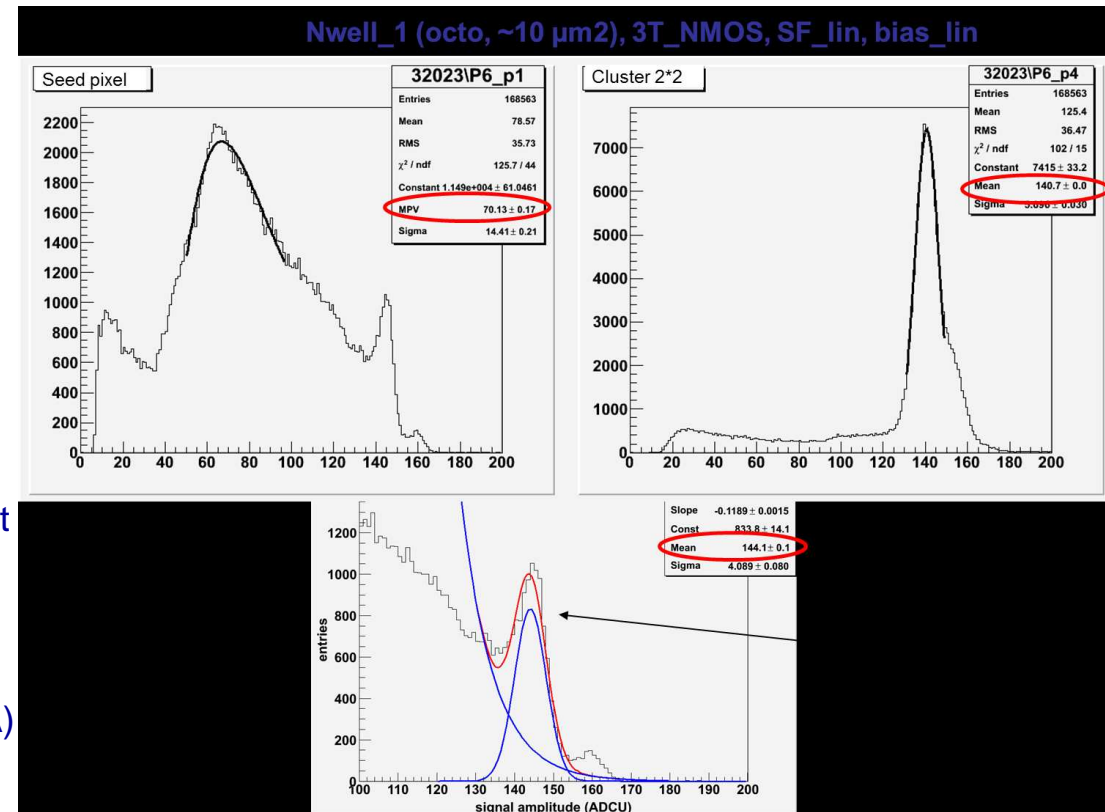
● MIMOSA-32 : technology exploration

- ✧ fabricated in Q4/2011 with high resistivity epitaxial layer
- ✧ numerous different pixels (sensing syst., pre-ampli., elongated pix.), etc.
- ✧ lab tests under way (^{55}Fe source)
 - good charge collection observed (high-res epi) but noise high
- ✧ beam tests foreseen in June-July '12



● Next steps

- ✧ Q3:
 - MIMOSA-22THR1 \equiv MIMOSA-30 translation
 - MIMOSA-22THR1 \equiv same with 2-discr/col.
- ✧ Q4:
 - AROM-1 \equiv Accelerated Read-Out MIMOSA sensor
 - prototype with in-pixel discrimination
 - SUZE-02 \equiv Zero-Suppression & output buffer circuit
 - sparsification: 4 rows simultaneous r.o.
- ✧ 2013: first full scale (1 cm^2) basic block fabrication
 - ⇒ final full size proto. in 2014/15 (ALICE, CBM, AIDA)



Characteristics & Variants of MIMOSA & AROM Sensors

- Assuming MIMOSA and AROM variants to equip innermost and outer layers
 - ※ MIMOSA-in and AROM-1 equip innermost layer
 - ※ MIMOSA-out and AROM-2 equip outer layers

Sensor version	MIMOSA-in	MIMOSA-out	AROM-1	AROM-2
Active area dimensions [mm ²]	8.7×31.0	19.6×31.0	10.9×31.0	20.8×31.0
Pixel dimensions [μm ²]	17×17	34×34	17×85	34×72
Single point resolution [μm]	≲ 3	≲ 4	5-7	~ 10
Read-out time [μs]	50	~ 100	1.5	7
Power consumption: instantaneous [W]	~ 1.8	~ 0.6	2.7	0.7
average [mW]	36	12	55	14

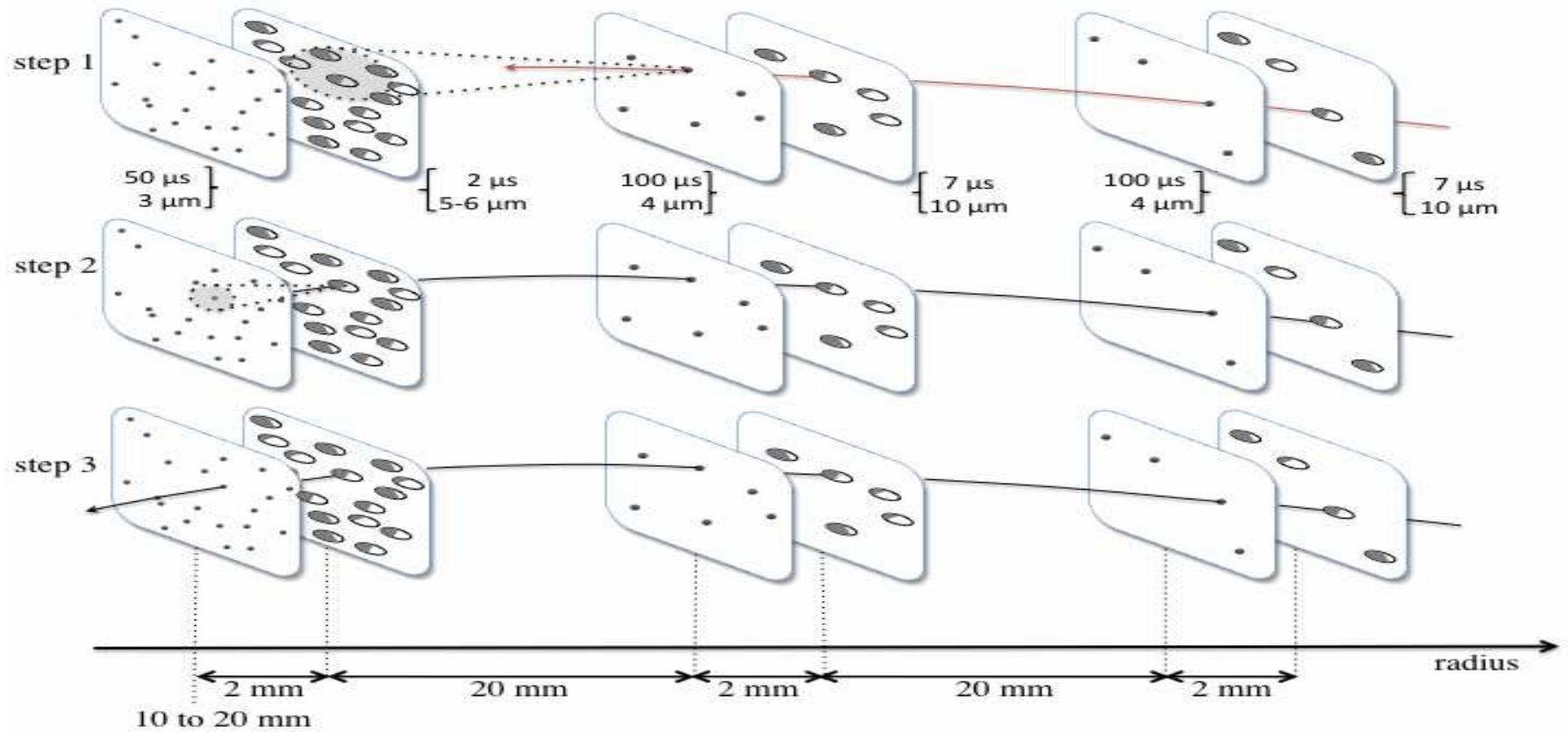
- Power consumption (average value stands for 5 ms long power-on periods ≡ 2% duty cycle):
 - ※ layer 1: 250 W (inst.) ⇒ 5 W (average)
 - ※ layer 2: 120 W (inst.) ⇒ 2.4 W (average)
 - ※ layer 3: 200 W (inst.) ⇒ 4 W (average)
- ⇒ Complete detector instantaneous power ≲ 600 W ⇒ <12 W in average

Tracking through ILD-VXD

- Tracking from outside towards IP combining MIMOSA spatial resolution & AROM timestamp

* MIMOSA provides < 3 or $4 \mu\text{m}$ spatial resolution

* AROM provides 2 or $7 \mu\text{s}$ time stamping



	M-in	A-1	M-out	A-2	M-out	A-2
Pixel occupancy [%] :	0.9	0.1	0.3	0.04	0.06	0.01
with safety factor 3 [%] :	2.6	0.3	0.9	0.1	0.2	0.03

VXD - SIT Variant Composed of CPS

- **ILD-SIT : baseline assumes 2 double-sided μ strip detector layers**
 - ✧ try understanding if CMOS sensors could improve performance with their high spatial resolution
 - ✧ advantage : spatial resolution $\triangleright 4 \times 4 \mu m^2$ instead of $7 \times 50 \mu m^2$
 - \Rightarrow improved soft track reconstruction (p) and TPC link
 - potentially : material budget, cost
 - ✧ disadvantage : time resolution $\triangleright 7 \mu s$ instead of $O(100)ns$ – Is power a pb ?
- **Variant of VXD–SIT design made of CMOS pixel sensors (other variants give similar performances)**

Layer	σ_{sp}	t_{int}	Occupancy [%]	Power
	MIMOSA/AROM	MIMOSA/AROM	w/o safety factor	inst./average
VXD-1	3 / 5-6 μm	50 / 2 μs	0.9(2.6) / 0.1(0.3)	250/5 W
VXD-2	4 / 10 μm	100 / 7 μs	0.3(0.9) / 0.04(0.1)	120/2.4 W
VXD-3	4 / 10 μm	100 / 7 μs	0.06(0.2) / 0.01(0.03)	200/4 W
SIT-1	4 / 15 μm	100 / 7 μs	$\lesssim 0.01$	~ 1.3 kW/26 W
SIT-2	4 μm	100 μs	$\lesssim 0.01$	~ 2.5 kW/50 W

- **ILD-SIT : power consumption (average $\lesssim 100$ W for $\gtrsim 4$ m² coverage) seems affordable**
 - \Rightarrow **need benchmark event study with beam BG to evaluate track reconstruction performance**

SUMMARY

- **Mature sensor architecture complies with all VXD specifications at $\sqrt{s}=500$ GeV :**
 - architecture based on sensors realised for EUDET-BT and STAR-PXL (0.35 μm CMOS process)
 - based on 2-sided ladder concept \Rightarrow hit resolution/timestamp on opposite ladder sides (PLUME project)
 - innermost layer : $< 3 \mu m$ and $\lesssim 10 \mu s$ (upgradable to $\lesssim 5 \mu s$ with 2 discri/col)
 - outer layers : $< 4 \mu m$ (ADCs not yet tested) and $\sim 100 \mu s$
 - VXD power consumption : < 700 W (inst.) / < 20 W (average)
 - final prototypes fabricated \Rightarrow tests under way : MIMOSA-30(in) & MIMOSA-31(out)
 - validation of concept \pm completed in 2012 with 2-sided ladder (PLUME) offering 0.35 % X_0 (X-section)
- **Translation 0.35 $\mu m \rightsquigarrow$ 0.18 μm CMOS under way for $\sqrt{s} \gtrsim 1$ TeV :**
 - benefits: read-out $< 2/10 \mu s$ (inner/outer layers), $> 20\%$ less power, sensor throughput, pixelated SIT, ...
 - exploratory chip (MIMOSA-32) under test
 - mid-scale prototypes validating architecture planned for submission in Q3/ & Q4/2012
 - Full Scale Basic Block (FSBB - 1cm^2 active area) expected to be fabricated in 2013
 - \Rightarrow Final (full scale) prototype in 2014/15
 - synergy with AIDA-SALAT, ALICE-ITS & -MFT, CMB-MVD, ...